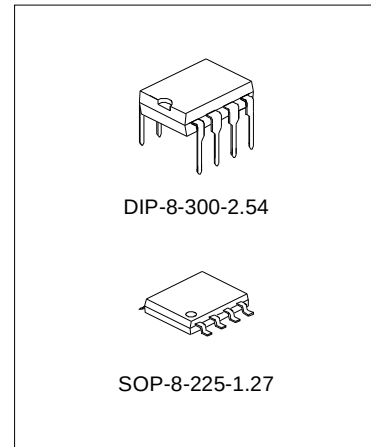


POWER FACTOR CORRECTION CONTROLLER OF CRITICAL DUCTING

DESCRIPTION

The SA7527 provides simple and high performance active power factor correction. The SA7527 is optimized for electronic ballasts and low power and high-density power supplies which require minimum board size, reduced external components and low power dissipation. Because the R/C filter is included in the current sense block, the external R/C filter is not necessary. Special circuitry has also been added to prevent no load runaway conditions. Regardless of the supply voltage, the output drive clamping circuit limits the overshoot of the power MOSFET gate drive. It greatly enhances the system reliability.



FEATURES

- * Internal start-up timer
- * Internal R/C filter eliminates the need for an external R/C filter
- * Very precise adjustable output over voltage protection
- * Zero current detector
- * One quadrant multiplier
- * Trimmed 1.5% internal band gap reference
- * Under voltage lockout with 3V of hysteresis
- * Totem pole output with high state clamp
- * Low start-up and operating current
- * 8-pin DIP or 8-pin SOP

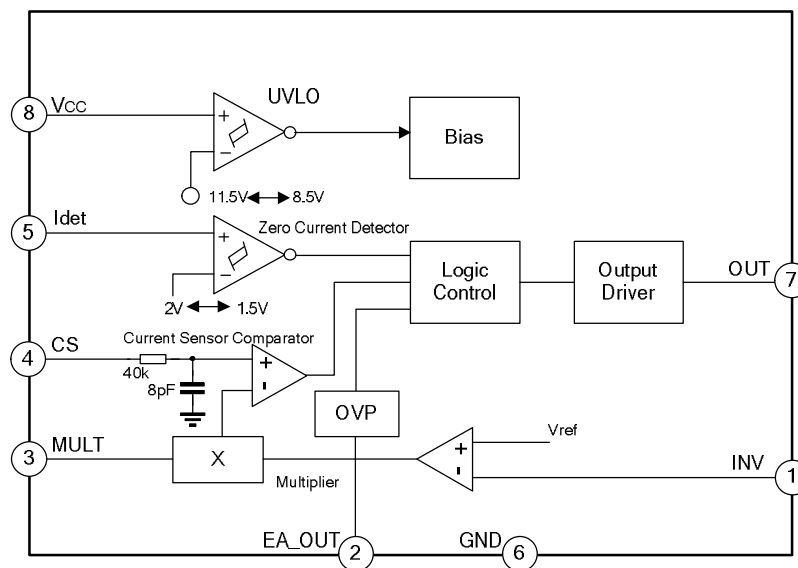
ORDERING INFORMATION

Device	Package
SA7527	DIP-8-300-2.54
SA7527S	SOP-8-225-1.27

APPLICATIONS

- * Electronic ballast
- * SMPS

BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS ($T_{amb}=25^{\circ}\text{C}$)

Characteristics	Symbol	Rating	Unit
Supply Voltage	VCC	30	V
Peak Drive Output Current	IOH, IOL	± 500	mA
Driver Output Clamping Diodes $V_O > V_{CC}$ or $V_O < -0.3\text{V}$	Iclamp	± 10	mA
Detector Clamping Diodes	Idet	± 10	mA
Error Amp, Multiplier And Comparator Input Voltage	Vin	-0.3 to 6	V
Operating Junction Temperature	Tj	150	$^{\circ}\text{C}$
Operating Temperature Range	Topr	-25 to 125	$^{\circ}\text{C}$
Storage Temperature Range	Tstg	-65 to 150	$^{\circ}\text{C}$
Power Dissipation	Pd	0.8	W

TEMPERATURE CHARACTERISTICS

Characteristics	Symbol	Min.	Typ.	Max.	Unit
Temperature Stability For Reference Voltage (Vref)	ΔV_{ref}	--	20	--	mV
Temperature Stability For Multiplier Gain (K)	$\Delta K/\Delta T$	--	-0.2	--	%/ $^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS (Unless otherwise stated, $V_{CC}=14\text{V}$, $-25^{\circ}\text{C} \leq T_{amb} \leq 125^{\circ}\text{C}$)

Characteristics	Symbol	Test condition	Min.	Typ.	Max.	Unit
Under Voltage Lockout Section						
Start Threshold Voltage	Vth (st)	VCC increasing	10.5	11.5	12.5	V
UVLO Hysteresis	HY (st)	--	2	3	4	V
Supply Current Section						
Start-Up Supply Current	Ist	$V_{CC}=V_{th(st)}-0.2$	10	60	100	μA
Operating Supply Current	ICC	Output not switching	--	3	6	mA
Operating Current OVP	ICC(OVP)	Vinv=3V	--	1.7	4	mA
Dynamic Operating Supply Current	IDCC	50kHz, CI=1nF	--	4	8	mA
Error Amplifier Section						
Voltage Feedback Input Threshold	Vref	Iref=0mA, Tamb=25 $^{\circ}\text{C}$	2.465	2.5	2.535	V
		-25 $\leq T_{amb} \leq 125^{\circ}\text{C}$	2.44	2.5	2.56	V
Line Regulation	ΔV_{ref1}	14V $\leq V_{CC} \leq 25\text{V}$	--	0.1	10	mV
Temperature Stability Of Vref (note)	ΔV_{ref3}	-25 $\leq T_{amb} \leq 125^{\circ}\text{C}$	--	20	--	mV
Input Bias Current	Ib(ea)	--	-0.5	--	0.5	μA
Output Source Current	Isorce	Vm2=4V	-2	-4	--	mA
Output Sink Current	Isink	Vm2=4V	2	4	--	mA
Output Upper Clamp Voltage (note)	Veao(H)	Isorce=0.1mA	--	6	--	V
Output Lower Clamp Voltage (note)	Veao(L)	Isink=0.1mA	--	2.25	--	V

(To be continued)

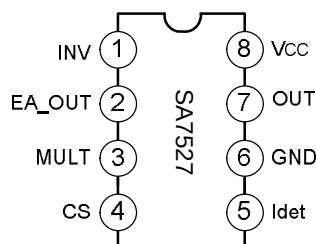
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Characteristics	Symbol	Test condition	Min.	Typ.	Max.	Unit
Large Signal Open Loop G gain (note)	Gv	--	60	80	--	dB
Power Supply Rejection Ratio (note)	PSRR	14V≤VCC≤25V	60	80	--	dB
Unity Gain Bandwidth (note)	GBW	--	--	1	--	MHz
Slew Rate (note)	SR	--	--	0.6	--	V/μs
Multiplier Section						
Input Bias Current (pin3)	Ib(m)	--	-0.5	--	0.5	μA
M1 Input Voltage Range (pin3)	ΔVm1	--	0	--	3.8	V
M2 Input Voltage Range (pin2)	ΔVm2	--	Vref	--	Vref+2.5	V
Multiplier Gain (note)	K	Vm1=1V, Vm2=3.5V	0.36	0.44	0.52	1/V
Maximum Multiplier Output Voltage	Vomax(m)	Vinv=0V, Vm1=4V	1.65	1.8	1.95	V
Temperature Stability Of K (note)	ΔK/ΔT	-25≤Tamb≤125°C	--	-0.2	--	%/°C
Current Sense Section						
Input Offset Voltage (note)	Vio(cs)	Vm1=0V, Vm2=2.2V	-10	3	10	mV
Input Bias Current	Ib(cs)	0V≤Vcs≤1.7V	-1	-0.1	1	μA
Current Sense Delay To Output (note)	td(cs)	--	--	200	500	ns
Zero Current Detect Section						
Input Voltage Threshold	Vth(det)	Vdet increasing	1.7	2	2.3	V
Detect Hysteresis	HY(det)	--	0.2	0.5	0.8	V
Input Low Clamp Voltage	Vclamp(l)	Idet=-100μA	0.45	0.75	1	V
Input High Clamp Voltage	Vclamp(h)	Idet=3mA	6.5	7.2	7.9	V
Input Bias Current	Ib(det)	1V≤Vdet≤5V	-1	-0.1	1	μA
Input High/Low Clamp Diode Current (note)	Iclamp(d)	--	--	--	±3	mA
Output Section						
Output Voltage High	Voh	Io=-10mA	10.5	11	--	V
Output Voltage Low	Voi	Io=10mA	--	0.8	1	V
Rising Time (note)	tr	CI=1nF	--	130	200	ns
Falling Time (note)	tf	CI=1nF	--	50	120	ns
Maximum Output Voltage	Vomax(o)	VCC=20V, Io=100μA	12	14	16	V
Output Voltage With UVLO Activated	Vomin(o)	VCC=5V, Io=100μA	--	--	1	V
Restart Timer Section						
Restart Time Delay	td(rst)	Vm1=1V, Vm2=3.5V	--	150	--	μs
Over Voltage Protection Section						
Soft OVP Detecting Current	Isovp	--	25	30	35	μA
Dynamic OVP Detecting Current	Ildovp	--	35	40	45	μA
Static OVP Threshold Voltage	Vovp	Vinv=2.7V	2.1	2.25	2.4	V

Note: These parameters, although guaranteed, are not 100% tested in production.

$$\text{Multiplier gain: } k = \frac{\text{pin4_threshold}}{V_{m1} \times (V_{m2} - V_{ref})} \dots (V_{m1} = V_{pin3}, V_{m2} = V_{pin2})$$

PIN CONFIGURATIONS

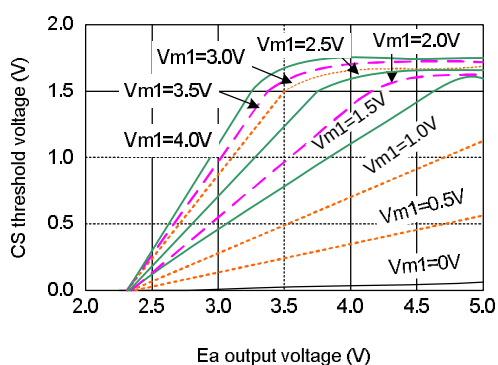


PIN DESCRIPTIONS

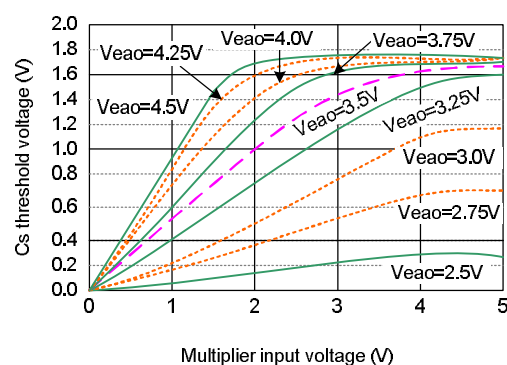
Pin no.	Pin name	Description
1	INV	Inverting input of the error amplifier. The output of the boost converter should be resistively divided to 2.5V and connected to this pin.
2	EA_OUT	The output of the error amplifier. A feedback compensation network is placed between this pin and the INV pin.
3	MULT	Input to the multiplier stage. The full-wave rectified AC voltage is divided to less than 2V and is connected to this pin.
4	CS	Input of the PWM comparator. The MOSFET current is sensed by a resistor and the resulting voltage is applied to this pin. An internal R/C filter is included to reject any high frequency noise.
5	Idet	Zero current detection input.
6	GND	The ground potential of all the pins.
7	OUT	Gate driver output. The push pull output stage is able to drive the Power MOSFET with peak current of 500mA.
8	VCC	Supply voltage of driver and control circuits.

ELECTRICAL CHARACTERISTICS CURVES

**Figure 1. Error Amplifier Output Voltage
vs Current Sensing Threshold**



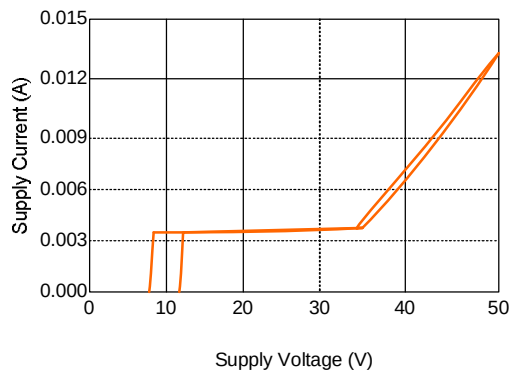
**Figure 2. Multiplier Input Voltage
vs Current Sensing Threshold**



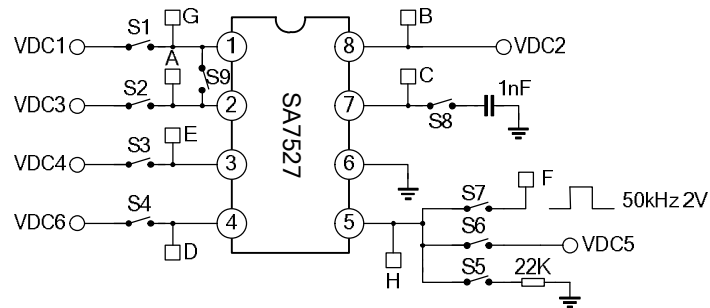
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Figure 3. Supply Current vs Supply Voltage



TEST CIRCUIT



TEST SPECIFICATION (Unless otherwise specified, VDC2=14V)

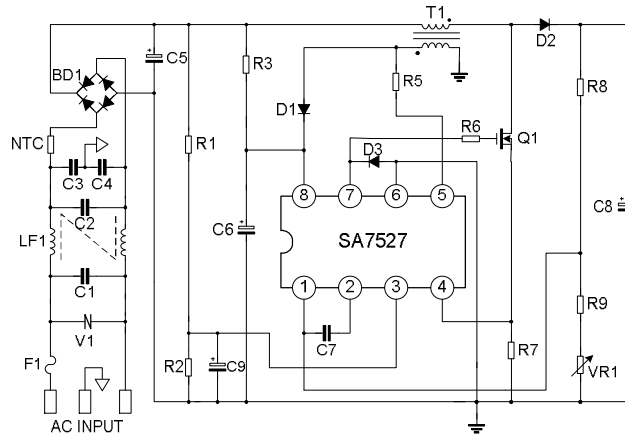
Parameter	Switches	Test conditions	Test point	Remark
$V_{th(st)}$	S2,S3,S4,S5	VDC3=3,VDC4=1,VDC6=0	B	VDC2 increase
$H_{Y(st)}$	S2,S3,S4,S5	VDC3=3,VDC4=1,VDC6=0	B	Following above, decrease the VDC2 until C level changed
$I_{(st)}$	S2,S3,S4,S5	VDC3=3,VDC4=1,VDC6=0	B	$VDC2 = V_{th(st)} - 0.2$
$I_{(cc)}$	S2,S3,S4,S5	VDC3=3,VDC4=1,VDC6=0	B	--
$I_{cc(ovp)}$	S1	VDC1=3	B	--
I_{dcc}	S1,S3,S4,S7,S8	VDC6=0	B	Input 50kHz/2V square wave to F
V_{ref}	S9	--	G	
ΔV_{ref}	S9	--	G	VDC2=14V、25V
$I_{b(ea)}$	S1	VDC1 change	G	--
$I_{(source)}$	S1,S2	VDC1=0,VDC3=4	A	--
$I_{(sink)}$	S1,S2	VDC1=3,VDC3=4	A	--
$V_{eao(H)}$	S1	VDC1=0	A	The source current of A is 1mA
$V_{eao(L)}$	S1	VDC1=3	A	The sink current of A is 1mA
$I_{b(m)}$	S3	--	E	VDC4: 0~4V

(To be continued)

(Continued)

Parameter	Switches	Test conditions	Test point	Remark
ΔV_{m1}	S1,S3,S4,S5	VDC1=2, initialize VDC4,VDC6 low level, enable C high level	E	Increasing the VDC6 and VDC4, enables the C changes until the VDC4 change do not affect the C level.
ΔV_{m2}	S1,S2,S3,S4,S5	VDC1=2,VDC4=1, initialize VDC3, VDC6 low level, enable C high level.	A	Increasing the VDC6 and VDC3 level, enables the C changes until the VDC3 change do not affect the C level.
K	S1,S2,S3,S4	VDC1=2V,VDC3=3.5,VDC4=1V	--	Increase the VDC6 until C level changed. $K=VDC6/(VDC3*VDC4)$
Vomax	S1,S3,S4,S5	VDC1=2V, VDC4=4	D	Increase the VDC6 until C level changed.
Ib(cs)	S4	--	D	VDC6:0~1.7V
Vth(det)	S1,S2,S3,S4,S6	VDC1=2V, VDC3=3,VDC4=1, VDC6=0,	G	Increase the VDC5 until C level changed.
HY(det)	S1,S2,S3,S4,S6	VDC1=2V, VDC3=3,VDC4=1, VDC6=0,	G	Following above, the VDC5 decreases until C level changed.
Vclamp(L)	--	--	G	Input 100 μ A to G
Vclamp(H)	--	--	G	Output 3mA from G
Ib(det)	S6	--	G	VDC5:1~5V
Voh	S1,S2,S3,S4,S5	VDC1=2,VDC6=0	C	Output 10mA from C
Vol	S1,S2,S3,S4,S5	VDC1=2,VDC6=2	C	Input 10mA to C
tr	S1,S2,S3,S4,S7	VDC1=2,VDC6=0	C	Input 50kHz/2V square wave to F
tf	S1,S2,S3,S4,S7	VDC1=2,VDC6=0	C	Input 50kHz/2V square wave to F
Vomax(o)	S1,S2,S3,S4,S5	VDC1=2,VDC2=20	C	Output 100 μ A from C
Vomin(o)	S1,S2,S3,S4,S5	VDC1=2,VDC2=5	C	Output 100 μ A from C
td(rst)	S1,S2,S3,S5	VDC1=2,VDC3=3.5,VDC4=1	C	Input 10kHz, 10 μ s, 2V narrow pulse to D (note1)
Isovp	S1,S3,S4,S5	VDC1=2,VDC6=0	A	Input static current to A, and enables C low level.
Idovp	S1,S3,S4,S5	VDC1=2,VDC6=0	A	Input dynamic current to A, and enable C low level.
Vovp	S1,S2,S3,S4,S5	VDC1=2.7,VDC4=1,VDC6=0	A	Increase the VDC3 until C level changed.
tf	S1,S2,S3,S4,S7	VDC1=2,VDC6=0	C	Input 50kHz/2V square wave to F

TYPICAL APPLICATION CIRCUIT



Note: The circuit and parameters are reference only, please set the parameters of the real application circuit based on the real test .

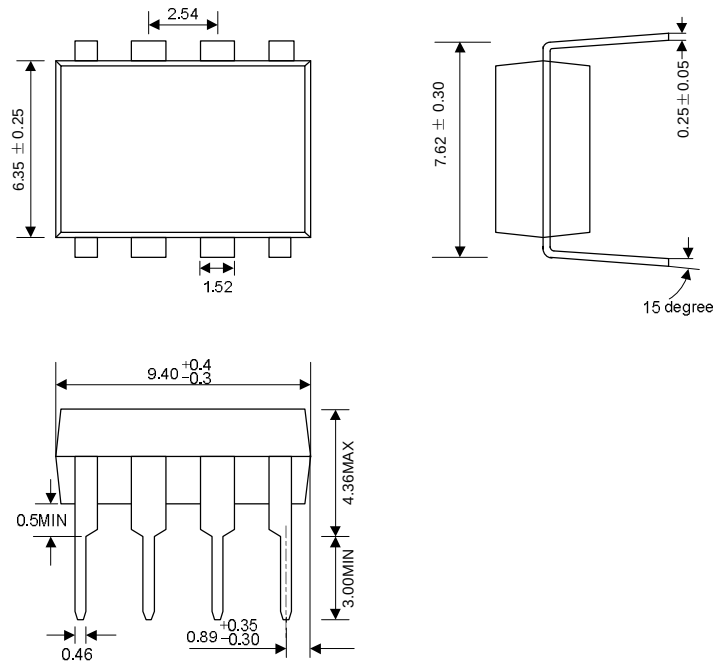
APPLICATION CIRCUIT COMPONENTS LIST

Part Number	Value	Note	Manufacturer
R1	1.8M Ω	1/4W	-
R2	18k Ω	1/4W	-
R3	120k Ω	1W	-
R5	22k Ω	1/4W	-
R6	10 Ω	1/4W	-
R7	3.0 Ω	1W	-
R8	1M Ω	1/4W	-
R9	6k Ω	1/4W	-
VR1	103	Variable resistor	-
C1	47nF, 275vac	Box-Cap	-
C2	100nF, 275vac	Box-Cap	-
C3,4	2200pF, 3000V	Y-Cap	-
C5	0.1 μ F, 630V	Miller-Cap	-
C6	47 μ F, 35V	Electrolytic	-
C7	1 μ F	MLCC	-
C8	22 μ F, 450V	Electrolytic	-
C9	1nF, 25V	Ceramic	-
BD1	600V/4A	Bridge Diode	-
D1,3	75V, 150mA	IN4148	-
D2	600V, 1A	BYV26C	-
LF1	45mH	Line Filter	-
T1	1.76mH(122T:10T)	EI2219	-
Q1	500V, 2.3A	FQPF4N50	Fairchild
F1	250V, 3A	Fuse	-
V1	470V	471	-
NTC	10 Ω	10D09	-

PACKAGE OUTLINE

DIP-8-300-2.54

UNIT: mm



SOP-8-225-1.27

UNIT: mm

